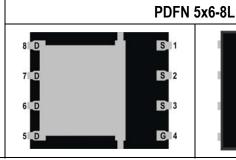
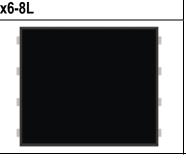
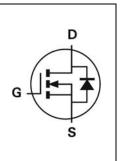


60V N-Channel Power MOSFET

 $V_{DSS}$  , 60V  $R_{DS(ON)}$  ,  $5.5m\Omega$  (max.) @  $V_{GS}\text{=}10V$   $I_D$  , 100A







Description	Features
The SG60N02Q uses advanced Trench technology and designs to provide excellent R <sub>DS(ON)</sub> with low gate charge. This device is suitable for use in PWM, load switching and general purpose applications.	<ul> <li>Low On-Resistance</li> <li>Low Input Capacitance</li> <li>Low Miller Charge</li> <li>Pb-free lead plating; RoHS compliant</li> </ul>
	Applications
	<ul> <li>Lithium-lon Secondary Batteries</li> <li>Load Switch</li> <li>DC-DC converters and Off-line UPS</li> </ul>

**Ordering Information** 

Ordering Code	RoHS Status	Package	Package Code	Packing	Quantity
SG60N02Q	Halogen-Free	PDFN 5*6-8L	Q	Tape & Reel	2,500

Absolute Maximum Ratings (T<sub>A</sub>=25°C unless otherwise noted)

Parame	ter	Symbol	Value	Unit
Drain-Source Voltage		V <sub>DS</sub>	60	V
Gate-Source Voltage		V <sub>GS</sub>	±20	V
Drain Current Continuous	T <sub>C</sub> =25°C	I-	100	Α
Drain Current-Continuous	Tc=70°C	I <sub>D</sub>	80	Α
Drain Current-Pulsed Note 1, 3		I <sub>DM</sub>	240	Α
Drain Current-Continuous	T <sub>A</sub> =25°C	I-	16	Α
Drain Current-Continuous	T <sub>A</sub> =70°C	I <sub>D</sub>	13	Α
Avalanche Current, L=0.1mH		I <sub>AS</sub>	53	Α
Avalanche Energy, L=0.1mH		E <sub>AS</sub>	140	mJ
	T <sub>C</sub> =25°C		83	W
Mayimum Dayyar Dissination	Tc=70°C	D.	53	W
Maximum Power Dissipation	T <sub>A</sub> =25°C	PD	2.3	W
	T <sub>A</sub> =70°C		1.5	W
Storage Temperature Range		T <sub>STG</sub>	-55 to +150	°C
Operating Junction Temperature Range		TJ	-55 to +150	°C

**Thermal Resistance Ratings** 

Parameter	Symbol	Conditions	Min.	Тур.	Max.	Unit
Maximum Junction-to-Ambient	$R_{\theta JA}$	Steady State	-	=	55	°C/W
Maximum Junction-to-Case	Rejc	Steady State	-	-	1.5	°C/W

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# **SG60N02Q**

60V N-Channel Power MOSFET

# Electrical Characteristics (T<sub>J</sub>=25°C unless otherwise noted)

OFF CHARACTERISTICS						
Parameter	Symbol	Conditions	Min.	Тур.	Max.	Unit
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	V <sub>GS</sub> =0V, I <sub>DS</sub> =250µA	60	-	-	V
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> =48V, V <sub>GS</sub> =0V	-	-	1	μΑ
Gate-Body Leakage	Igss	V <sub>GS</sub> =±20V, V <sub>DS</sub> =0V	-	ī	±100	nA

ON CHARACTERISTICS						
Parameter	Symbol	Conditions	Min.	Тур.	Max.	Unit
Gate Threshold Voltage	V <sub>GS(TH)</sub>	V <sub>DS</sub> =V <sub>GS</sub> , I <sub>DS</sub> =250µA	2	3	4	V
Drain-Source On-State Resistance	R <sub>DS(ON)</sub>	V <sub>GS</sub> =10V, I <sub>DS</sub> =20A	-	-	5.5	mΩ

DYNAMIC CHARACTERISTICS						
Parameter	Symbol	Conditions	Min.	Тур.	Max.	Unit
Input Capacitance	C <sub>iss</sub>		-	4871	-	
Output Capacitance	Coss	V <sub>DS</sub> =30V, V <sub>GS</sub> =0V, f=1MHz	-	243	-	pF
Reverse Transfer Capacitance	C <sub>rss</sub>		-	124	-	
Gate Resistance	R <sub>g</sub>	V <sub>GS</sub> =0V, V <sub>DS</sub> =0V, f=1MHz	-	1.5	-	Ω

SWITCHING CHARACTERISTICS						
Parameter	Symbol	Conditions	Min.	Тур.	Max.	Unit
Turn-On Delay Time	T <sub>d(on)</sub>		-	25	-	
Rise Time	tr	V <sub>DD</sub> =30V, I <sub>D</sub> =30A, V <sub>GS</sub> =10V,	-	19	-	
Turn-Off Delay Time	T <sub>d(off)</sub>	R <sub>GEN</sub> =3Ω	-	85	-	ns
Fall Time	t <sub>f</sub>		-	43	-	
Total Gate Charge at 10V	Qg		-	118	-	
Gate to Source Gate Charge	Q <sub>gs</sub>	$V_{DS}$ =30V, $I_{DS}$ =30A, $V_{GS}$ =10V	-	28	-	nC
Gate to Drain "Miller" Charge	Q <sub>gd</sub>		-	45	-	

DRAIN-SOURCE DIODE CHARACTERISTICS AND MAXIMUM RATINGS						
Parameter Symbol Conditions Min. Typ. Max. Unit						Unit
Drain-Source Diode Forward Voltage	V <sub>SD</sub>	V <sub>GS</sub> =0V, I <sub>DS</sub> =20A	-	0.8	1.3	V
Body Diode Reverse Recovery Time	t <sub>rr</sub>	1 -204 dl/dt-1004/us	-	36	-	ns
Body Diode Reverse Recovery Charge	Qrr	I <sub>F</sub> =30A, dl/dt=100A/μs	-	53	-	nC

### Notes:

- 1. Pulse Test: Pulse Width ≤ 300µs, Duty Cycle ≤ 2%.
- 2. R<sub>BJA</sub> is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins. R<sub>BJC</sub> is guaranteed by design while R<sub>BCA</sub> is determined by the user's board design. R<sub>BJA</sub> shown below for single device operation on FR-4 in still air.

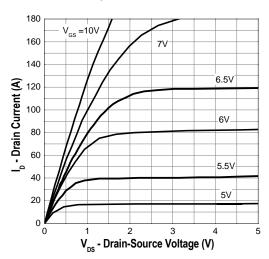


# **SG60N02Q**

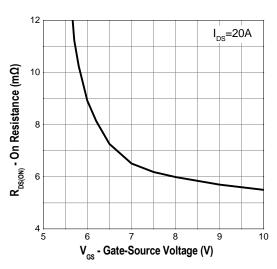
#### 60V N-Channel Power MOSFET

# **Typical Operating Characteristics**

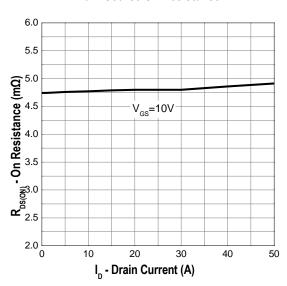
## **Output Characteristics**



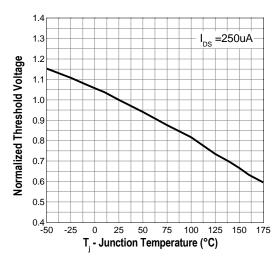
#### **Gate-Source On Resistance**



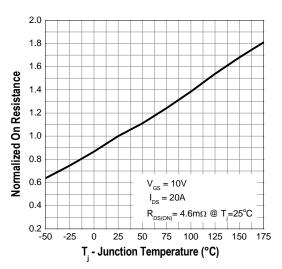
#### **Drain-Source On Resistance**



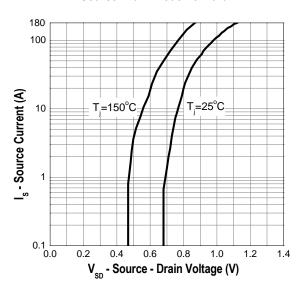
## **Gate Threshold Voltage**



#### **Drain-Source On Resistance**



#### Source-Drain Diode Forward



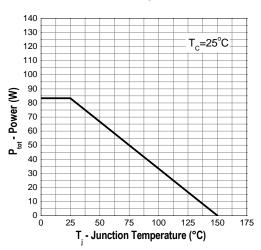


# SG60N02Q

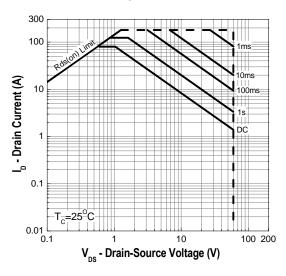
#### 60V N-Channel Power MOSFET

# **Typical Operating Characteristics (Cont.)**

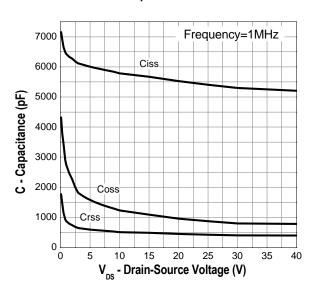
# **Power Dissipation**



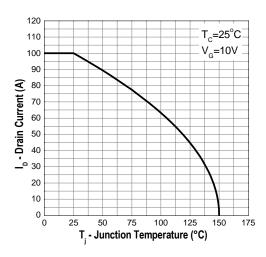
## **Safe Operation Area**



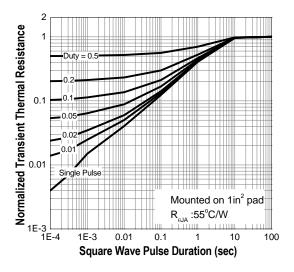
#### Capacitance



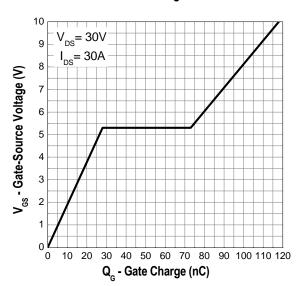
#### **Drain Current**



### **Transient Thermal Impedance**



## **Gate Charge**







# **Marking Information**

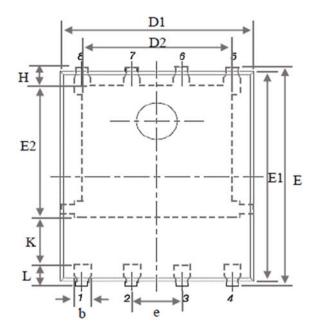
PDFN 5x6-8L (Q)	Marking Rule
Laser Marking	Line 1 : Device SG60N02Q
SG60N02Q YYMMXXX	Line 2: Date Code YYMMXXX  YY: Year Code MM: Month Code XXX: Serial Number
Diagram	



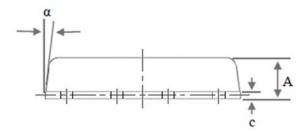


# Package of Dimension

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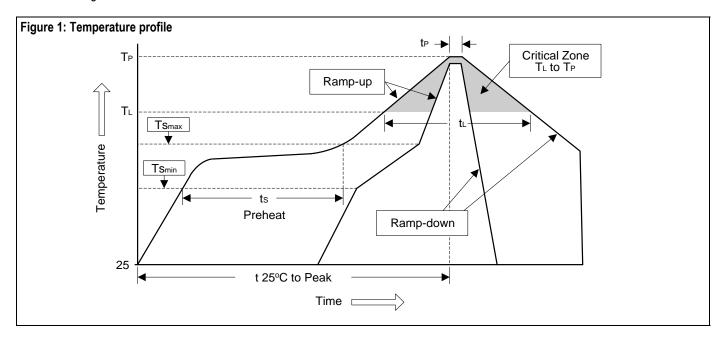
Symbol	Min	Nor	Max
Α	0.90	1.04	1.17
b	0.33	0.42	0.51
C	0.06	0.20	0.35
D1	4.80	5.10	5.40
D2	3.61	3.96	4.31
Е	5.90	6.03	6.15
E1	5.65	5.75	5.85
E2	3.30	3.54	3.78
е		1.27 BSC	
Н	0.38	0.50	0.61
L	0.38	0.55	0.71
L1	0.05	0.15	0.25





# Soldering Methods for Silicongear's Products

- 1. Storage environment: Temperature=10°C to 35°C Humidity=65%±15%
- 2. Reflow soldering of surface-mount devices



Profile Feature	Sn-Pb Eutectic Assembly	Pb-Free Assembly
Average ramp-up rate (T <sub>L</sub> to T <sub>P</sub> )	<3°C/sec	<3°C/sec
Preheat		
- Temperature Min (Ts <sub>min</sub> )	100°C	150°C
- Temperature Max (Ts <sub>max</sub> )	150°C	200°C
- Time (min to max) (ts)	60 to 120 sec	60 to 180 sec
Tsmax to T∟		
- Ramp-up Rate	<3°C/sec	<3°C/sec
Time maintained above:		
- Temperature (T <sub>L</sub> )	183°C	217°C
- Time (t∟)	60 to 150 sec	60 to 150 sec
Peak Temperature (T <sub>P</sub> )	240°C +0/-5°C	260°C +0/-5°C
Time within 5°C of actual Peak	10 to 30 sec	20 to 40 sec
Temperature (t <sub>P</sub> )	10 to 30 sec	20 to 40 Sec
Ramp-down Rate	<6°C/sec	<6°C/sec
Time 25°C to Peak Temperature	<6 minutes	<8 minutes

3. Flow (wave) soldering (solder dipping)

Products	Peak Temperature	Dipping Time
Pb devices.	245°C ±5°C	5sec ±1sec
Pb-Free devices.	260°C +0/-5°C	5sec ±1sec



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